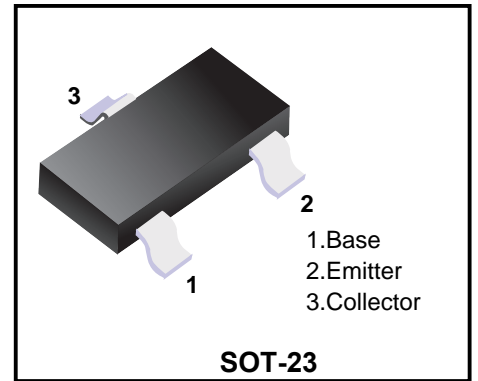


PNP Transistors

Features

- Ideally suited for automatic insertion
- Epitaxial planar die construction
- Complementary NPN type available(BC817)



Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-50	V
Collector - Emitter Voltage	V _{CEO}	-45	
Emitter - Base Voltage	V _{EBO}	-5	
Collector Current - Continuous	I _c	-0.5	A
Collector Power Dissipation	P _c	0.3	W
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

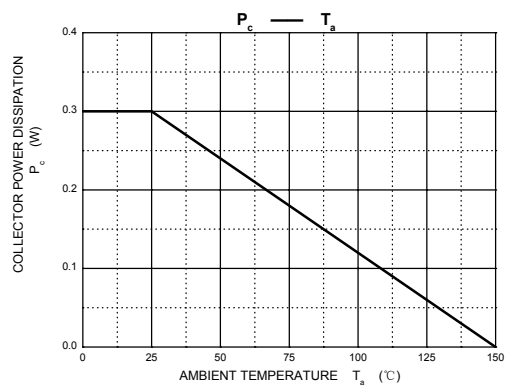
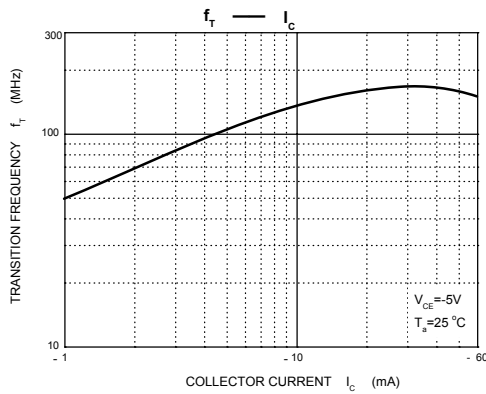
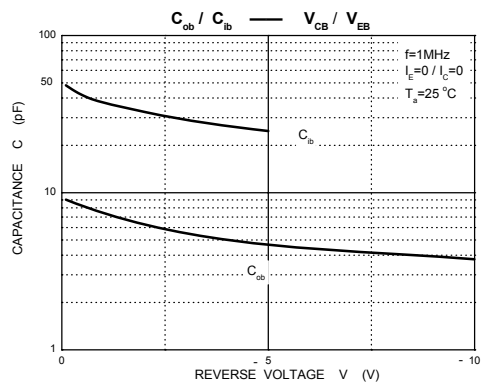
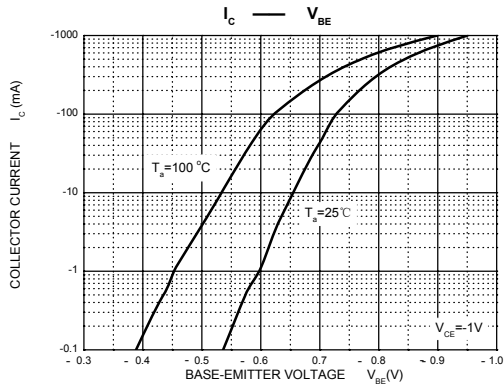
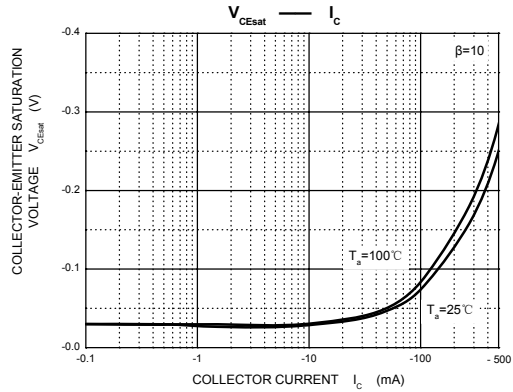
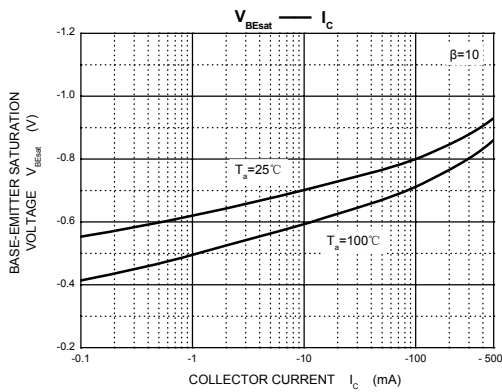
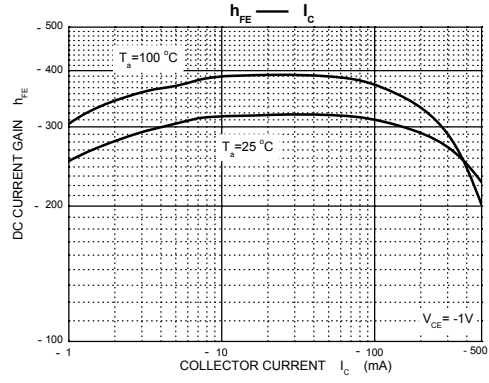
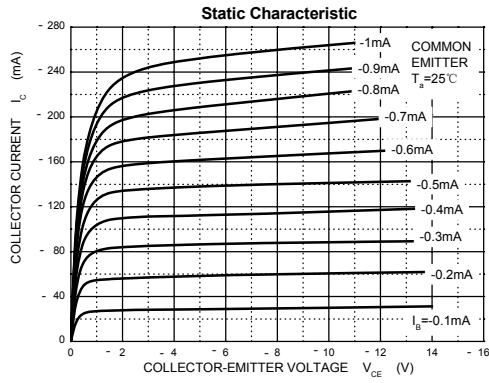
Electrical Characteristics (Ta=25°C unless otherwise specified.)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _c = -100 uA, I _E =0	-50			V
Collector- emitter breakdown voltage	V _{CEO}	I _c = -10 mA, I _B =0	-45			
Emitter - base breakdown voltage	V _{EBO}	I _E = -100 uA, I _c =0	-5			
Collector-base cut-off current	I _{CB0}	V _{CB} = -45 V, I _E =0			-0.1	uA
Collector- emittercut-off current	I _{CEO}	V _{CE} =- 40 V, I _B =0			-0.2	
Emitter cut-off current	I _{EBO}	V _{EB} = -4V, I _c =0			-0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =-500 mA, I _B =- 50mA			-0.7	V
Base - emitter saturation voltage	V _{BE(sat)}	I _c = -500 mA, I _B = -50mA			-1.2	
DC current gain	h _{fe} (1)	V _{CE} = -1V, I _c = -100mA	100		630	
	h _{fe} (2)	V _{CE} = -1V, I _c = -500mA	40			
Transition frequency	f _t	V _{CE} = -5V, I _c = -10mA,f=100MHz	100			MHz

h_{FE} Classification

Rank	BC807-16	BC807-25	BC807-40
Range	100-250	160-400	250-630
Marking	5A	5B	5C

Typical Characteristics



Ordering information

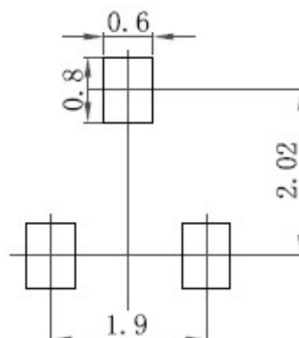
Package	Packing Description	Base Quantity	Packing Quantity
SOT-23	Tape/Reel,7"reel	3000pcs/Reel	24000PCS/Box 120000PCS/Carton

Package Dimensions

SOT-23

Dim.	Millimeter (mm)		mil	
	Min.	Max.	Min.	Max.
A	0.9	1.15	35	45
A1	0.1		3.9	
bp	0.38	0.48	15	19
C	0.09	0.15	3.54	5.9
D	2.8	3.0	110	118
E	1.2	1.4	47	55
E	1.9		75	
E1	0.95		37	
HE	2.1	2.55	83	100
Lp	0.15	0.45	5.9	18
Q	0.45	0.55	18	22
v	0.2		7.9	
W	0.1		4	

The recommended mounting pad size



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